



KI SEMICONDUCTOR CO.

SOT-23 Plastic-Encapsulate Diodes

1SS184

SWITCHING DIODE

FEATURES

Power dissipation

$$P_D : 150 \text{ mW}(T_{amb}=25^\circ\text{C})$$

Forward Current

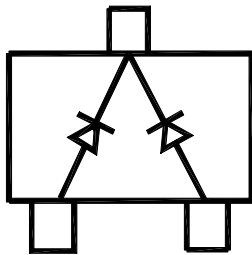
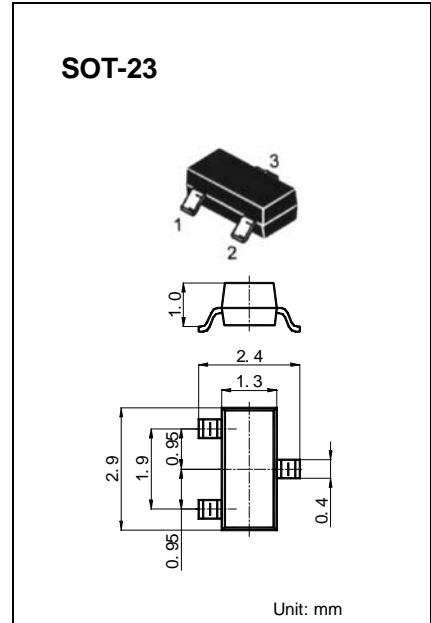
$$I_F : 100 \text{ mA}$$

Reverse Voltage

$$V_R: 80 \text{ V}$$

Operating and storage junction temperature range

$$T_{J, T_{stg}}: -55^\circ\text{C to } +150^\circ\text{C}$$



Marking B3

ELECTRICAL CHARACTERISTICS($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	80		V
Reverse voltage leakage current	I_R	$V_R=80\text{V}$		0.5	μA
Forward voltage	V_F	$I_F=100\text{mA}$		1.2	V
Diode capacitance	C_D	$V_R=0\text{V}$ $f=1\text{MHz}$		3	pF
Reverse recovery time	t_{rr}			4	nS